G2N4403

PNP EPITAXIAL PLANAR TANSISTOR

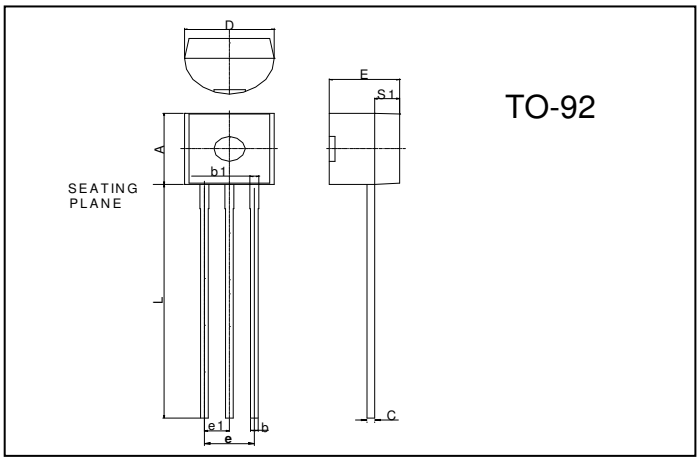
Description

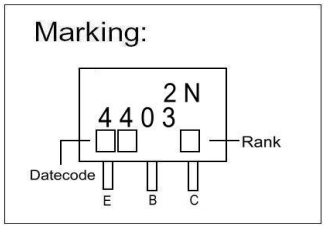
The G2N4403 is designed for general purpose switching and amplifier applications.

Features

*Complementary to G2N4401
*High Power Dissipation: 625mW at 25℃
*High DC Current Gain: 100-300 at 150mA
*High Breakdown Voltage: 40V Min

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Total Power Dissipation	P_D	625	mW

Characteristics at Ta = 25℃

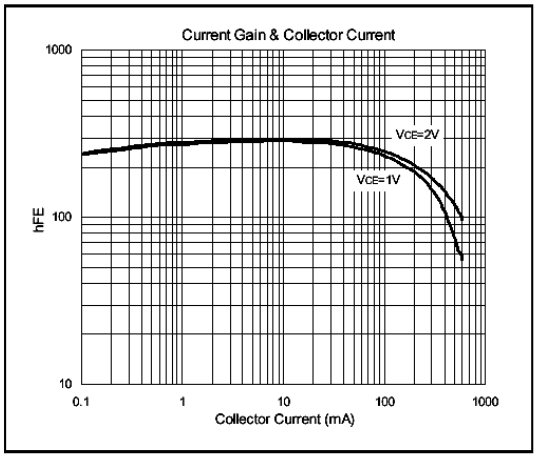
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-40	-	-	V	I_C=-100uA
BV_{CEO}	-40	-	-	V	I_C=-1mA
BV_{EBO}	-5	-	-	V	I_E=-10uA
ICEX	-	-	-100	nA	V_{CE}=-35V, V_{BE}= -0.4V
*V_{CE}(sat)1	-	-	-0.4	V	I_C=-150mA, I_B=-15mA
*V_{CE}(sat)2	-	-	-750	mV	I_C=-500mA, I_B=-15mA
*V_{BE}(sat)1	-750	-	-950	mV	I_C=-150mA, I_B=-15mA
*V_{BE}(sat)2	-	-	-1.3	V	I_C=-500mA, I_B=-50mA
*hFE1	30	-	-		V_{CE}=-1V, I_B=-0.1mA
*hFE2	60	-	-		V_{CE}=-1V, I_C=-1mA
*hFE3	100	-	-		V_{CE}=-1V, I_C=-10mA
*hFE4	100	-	300		V_{CE}=-2V, I_C=-150mA
*hFE5	20	-	-		V_{CE}=-2V, I_C=-500mA
fT	200	-	-	MHz	V_{CE}=-10V, I_C=-20mA, f=100MHz
Cob	-	-	8.5	pF	V_{CB}=-10V, f=1MHz

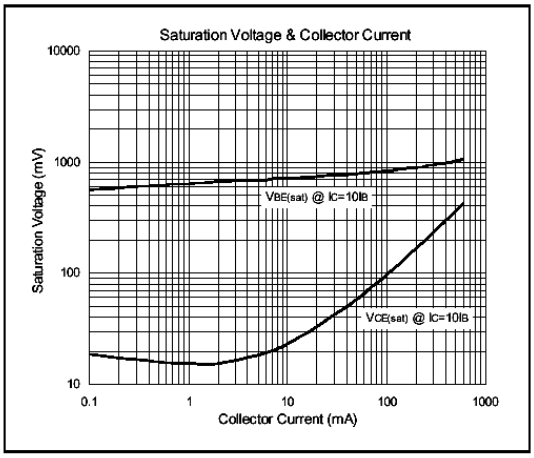
Classification OF h_{FE4}

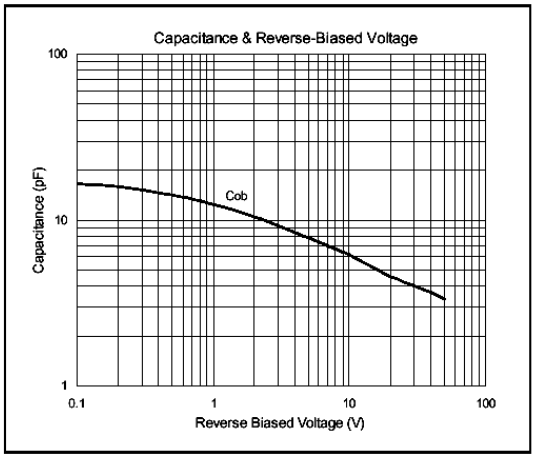
* Pulse Test: Pulse Width≦380us, Duty Cycle≦2%

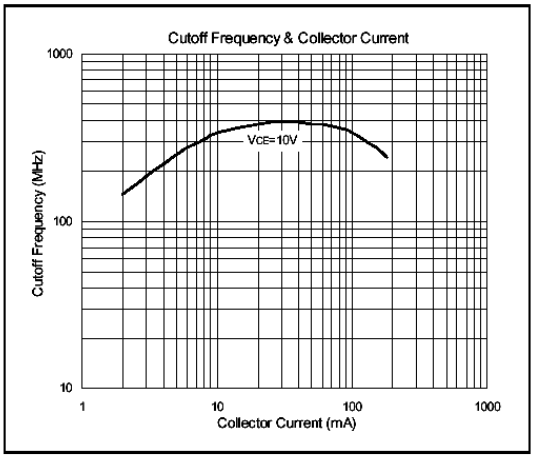
Rank	A	B
Range	100-210	190-300

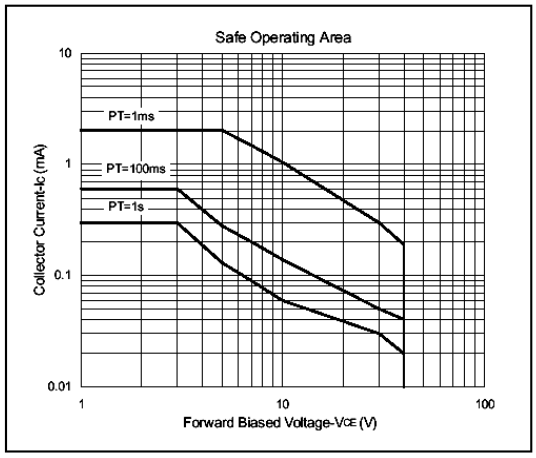
Characteristics Curve











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